

## UCC28700-Q1 具有一次侧稳压功能的恒压、恒流控制器

### 1 特性

- 符合汽车应用要求
- 具有符合 AEC-Q100 的下列结果：
  - 器件温度等级 1:  $-40^{\circ}\text{C}$  至  $125^{\circ}\text{C}$
  - 器件人体模型 (HBM) 分类等级 2:  $\pm 2\text{kV}$
  - 器件充电器件模型 (CDM) 分类等级 C4B: 750V
- 小于 30mW 的待机功耗
- 初级端调节 (PSR) 免除了对光耦合器的需要
- $\pm 5\%$  电压和电流调节
- 130kHz 最大开关频率
- 针对最高总体效率的准谐振谷值开关运行
- 用来减少电磁干扰 (EMI) 兼容的频率抖动机制 (正在申请专利)
- 宽 VDD 范围允许使用小型偏置电容器
- 针对金属氧化物半导体场效应晶体管 (MOSFET) 的已钳制栅极驱动输出
- 保护功能: 过压、欠压和过流
- 可编程电缆补偿
- 小外形尺寸晶体管 (SOT) 23-6 封装

### 2 应用

- 汽车 AC-DC 和 DC-DC 电源转换
- 混合动力汽车 (HEV) 中汽车动力传动系统的辅助电源
- 反激和降压电源转换器

### 3 说明

UCC28700-Q1 反激电源控制器无需使用光耦合器即可提供恒定电压 (CV) 和恒定电流 (CC) 输出稳压。此器件处理来自一次侧电源开关和辅助反激式绕组的信息, 以对输出电压和电流进行精确控制。此器件具有低启动电流、动态控制工作状态以及定制调制配置文件诸多优势, 因此可实现超低功耗, 并且不会影响启动时间或输出瞬态响应。

UCC28700-Q1 所采用的控制算法使得工作效率符合甚至超过现行标准。输出驱动接至一个 MOSFET 电源开关。带有谷值开关的断续传导模式 (DCM) 减少了开关损耗。开关频率的调制和初级电流峰值振幅 (FM 和 AM) 在整个负载和线路范围内保持较高的转换效率。

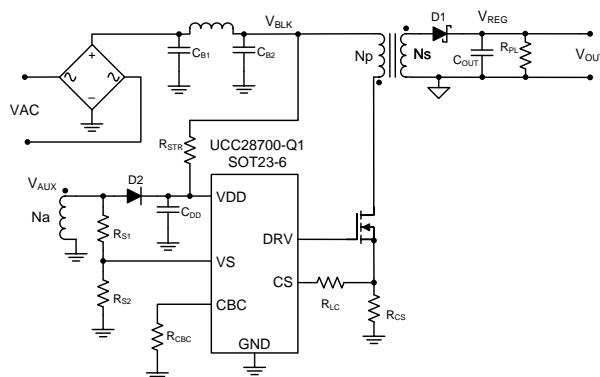
此控制器有一个 130kHz 的最大开关频率并且一直保持对变压器内初级峰值电流的控制。保护特性有助于保持控制中的初级和次级应力分量。UCC28700-Q1 可对电缆补偿的电平进行编程。

#### 器件信息<sup>(1)</sup>

器件型号	封装	封装尺寸 (标称值)
UCC28700-Q1	SOT-23 (6)	2.90mm x 1.60mm

(1) 如需了解所有可用封装, 请见数据表末尾的可订购产品附录。

典型应用电路原理图



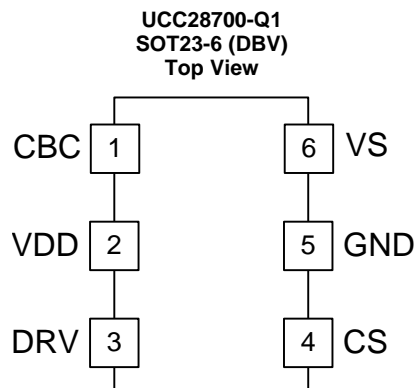
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## 4 修订历史记录

日期	修订版本	注释
2015 年 1 月	*	最初发布。

## 5 Pin Configuration and Functions



### Pin Functions

PIN		I/O	DESCRIPTION
NAME	UCC28700-Q1 NO.		
CBC	1	I	Cable Compensation (CBC) is a programming pin for compensation of cable voltage drop. Cable compensation is programmed with a resistor to GND.
CS	4	I	Current Sense (CS) input connects to a ground-referenced current-sense resistor in series with the power switch. The resulting voltage is used to monitor and control the peak primary current. A series resistor can be added to this pin to compensate the peak switch current levels as the AC-mains input varies.
DRV	3	O	Drive (DRV) is an output used to drive the gate of an external high voltage MOSFET switching transistor.
GND	5	—	The Ground (GND) pin is both the reference pin for the controller and the low-side return for the drive output. Special care should be taken to return all AC decoupling capacitors as close as possible to this pin and avoid any common trace length with analog signal return paths.
VDD	2	—	VDD is the bias supply input pin to the controller. A carefully-placed bypass capacitor to GND is required on this pin.
VS	6	I	Voltage Sense (VS) is an input used to provide voltage and timing feedback to the controller. This pin is connected to a voltage divider between an auxiliary winding and GND. The value of the upper resistor of this divider is used to program the AC-mains run and stop thresholds and line compensation at the CS pin.

## 6 Specifications

### 6.1 Absolute Maximum Ratings<sup>(1)</sup>

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
Bias supply voltage	$V_{VDD}$		38	V
Continuous gate current sink	$I_{DRV}$		50	mA
Continuous gate current source	$I_{DRV}$		Self-limiting	
Peak VS pin current	$I_{VS}$		-1.2	
Gate-drive voltage at DRV	$V_{DRV}$	-0.5	Self-limiting	V
Voltage range	VS	-0.75	7	
	CS, CBC	-0.5	5	
Operating junction temperature range	$T_J$	-55	150	°C
Lead temperature 0.6 mm from case for 10 seconds			260	
Storage temperature, $T_{stg}$		-65	150	°C

- (1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under [Recommended Operating Conditions](#) is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. All voltages are with respect to GND. Currents are positive into, negative out of the specified terminal. These ratings apply over the operating ambient temperature ranges unless otherwise noted.

### 6.2 ESD Ratings

		VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per AEC Q100-002 <sup>(1)</sup>	±2000
		Charged-device model (CDM), per AEC Q100-011	±750

- (1) AEC Q100-002 indicates that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

### 6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
VDD	Bias supply operating voltage	9	35	V
$C_{VDD}$	VDD bypass capacitor	0.047	1	μF
$R_{CBC}$	Cable-compensation resistance	10		kΩ
$I_{VS}$	VS pin current	-1		mA
$T_J$	Operating junction temperature	-40	125	°C

## 6.4 Thermal Information

THERMAL METRIC <sup>(1)</sup>		UCC28700-Q1		UNIT
		DBV		
		6 PINS		
$\theta_{JA}$	Junction-to-ambient thermal resistance <sup>(2)</sup>	180		°C/W
$\theta_{JCTop}$	Junction-to-case (top) thermal resistance <sup>(3)</sup>	71.2		
$\theta_{JB}$	Junction-to-board thermal resistance <sup>(4)</sup>	44.4		
$\psi_{JT}$	Junction-to-top characterization parameter <sup>(5)</sup>	5.1		
$\psi_{JB}$	Junction-to-board characterization parameter <sup>(6)</sup>	43.8		

- (1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, [SPRA953](#).
- (2) The junction-to-ambient thermal resistance under natural convection is obtained in a simulation on a JEDEC-standard, high-K board, as specified in JESD51-7, in an environment described in JESD51-2a.
- (3) The junction-to-case (top) thermal resistance is obtained by simulating a cold plate test on the package top. No specific JEDEC-standard test exists, but a close description can be found in the ANSI SEMI standard G30-88.
- (4) The junction-to-board thermal resistance is obtained by simulating in an environment with a ring cold plate fixture to control the PCB temperature, as described in JESD51-8.
- (5) The junction-to-top characterization parameter,  $\psi_{JT}$ , estimates the junction temperature of a device in a real system and is extracted from the simulation data for obtaining  $R_{\theta JA}$ , using a procedure described in JESD51-2a (sections 6 and 7).
- (6) The junction-to-board characterization parameter,  $\psi_{JB}$ , estimates the junction temperature of a device in a real system and is extracted from the simulation data for obtaining  $R_{\theta JA}$ , using a procedure described in JESD51-2a (sections 6 and 7).

## 6.5 Electrical Characteristics

over operating free-air temperature range,  $V_{DD} = 25\text{ V}$ ,  $R_{CBC} = \text{open}$ ,  $-40^{\circ}\text{C} \leq T_A \leq 125^{\circ}\text{C}$ ,  $T_J = T_A$   
(unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNITS
<b>BIAS SUPPLY INPUT</b>						
$I_{RUN}$	Supply current, run	$I_{DRV} = 0$ , run state		2.10	2.65	mA
$I_{WAIT}$	Supply current, wait	$I_{DRV} = 0$ , wait state		85	110	$\mu\text{A}$
$I_{START}$	Supply current, start	$I_{DRV} = 0$ , $V_{VDD} = 18\text{ V}$ , start state		1.0	1.5	$\mu\text{A}$
$I_{FAULT}$	Supply current, fault	$I_{DRV} = 0$ , fault state		2.1	2.8	mA
<b>UNDER-VOLTAGE LOCKOUT</b>						
$V_{VDD(on)}$	VDD turn-on threshold	$V_{VDD}$ low to high	17.5	21.0	23.0	V
$V_{VDD(off)}$	VDD turn-off threshold	$V_{VDD}$ high to low	7.70	8.10	8.45	V
<b>VS INPUT</b>						
$V_{VSR}$	Regulating level	Measured at no-load condition, $T_J = 25^{\circ}\text{C}$	4.01	4.05	4.09	V
$V_{VSNC}$	Negative clamp level	$I_{VS} = -300\ \mu\text{A}$ , volts below ground	190	250	325	mV
$I_{VSB}$	Input bias current	$V_{VS} = 4\text{ V}$	-0.25	0	0.25	$\mu\text{A}$
<b>CS INPUT</b>						
$V_{CST(max)}$	Max CS threshold voltage	$V_{VS} = 3.7\text{ V}^{(1)}$	715	750	775	mV
$V_{CST(min)}$	Min CS threshold voltage	$V_{VS} = 4.35\text{ V}^{(1)}$	230	250	270	mV
$K_{AM}$	AM control ratio	$V_{CST(max)} / V_{CST(min)}$	2.75	3.00	3.15	V/V
$V_{CCR}$	constant-current regulating level	CC regulation constant	310	319	329	mV
$K_{LC}$	Line compensating current ratio	$I_{VSL} = -300\ \mu\text{A}$ , $I_{VSL} / \text{current out of CS pin}$	23	25	28	A/A
$T_{CSLEB}$	Leading-edge blanking time	DRV output duration, $V_{CS} = 1\text{ V}$	195	235	275	ns
<b>DRV</b>						
$I_{DRS}$	DRV source current	$V_{DRV} = 8\text{ V}$ , $V_{VDD} = 9\text{ V}$	20	25		mA
$R_{DRVLS}$	DRV low-side drive resistance	$I_{DRV} = 10\text{ mA}$		6	12	$\Omega$
$V_{DRCL}$	DRV clamp voltage	$V_{VDD} = 35\text{ V}$		14	16	V
$R_{DRVSS}$	DRV pull-down in start state		150	200	230	k $\Omega$
<b>PROTECTION</b>						

- (1) These devices automatically vary the control frequency and current sense thresholds to improve EMI performance, these threshold voltages and frequency limits represent average levels.

## Electrical Characteristics (接下页)

over operating free-air temperature range,  $V_{DD} = 25\text{ V}$ ,  $R_{CBC} = \text{open}$ ,  $-40^{\circ}\text{C} \leq T_A \leq 125^{\circ}\text{C}$ ,  $T_J = T_A$   
(unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNITS
$V_{OVP}$	Over-voltage threshold	At VS input, $T_J = 25^{\circ}\text{C}$	4.52	4.60	4.68	V
$V_{OCP}$	Over-current threshold	At CS input	1.4	1.5	1.6	
$I_{VSL(\text{run})}$	VS line-sense run current	Current out of VS pin – increasing	190	220	260	$\mu\text{A}$
$I_{VSL(\text{stop})}$	VS line-sense stop current	Current out of VS pin – decreasing	70	80	95	
$K_{VSL}$	VS line-sense ratio	$I_{VSL(\text{run})} / I_{VSL(\text{stop})}$	2.50	2.80	3.05	A/A
$T_{J(\text{stop})}$	Thermal shut-down temperature	Internal junction temperature		165		$^{\circ}\text{C}$
<b>CABLE COMPENSATION</b>						
$V_{CBC(\text{max})}$	Cable compensation maximum voltage	Voltage at CBC at full load	2.8	3.0	3.4	V
$V_{CVS(\text{min})}$	Compensation at VS	$V_{CBC} = \text{open}$ , change in VS regulating level at full load	-45	-15	25	mV
$V_{CVS(\text{max})}$	Maximum compensation at VS	$V_{CBC} = 0\text{ V}$ , change in VS regulating level at full load	275	320	365	

## 6.6 Switching Characteristics

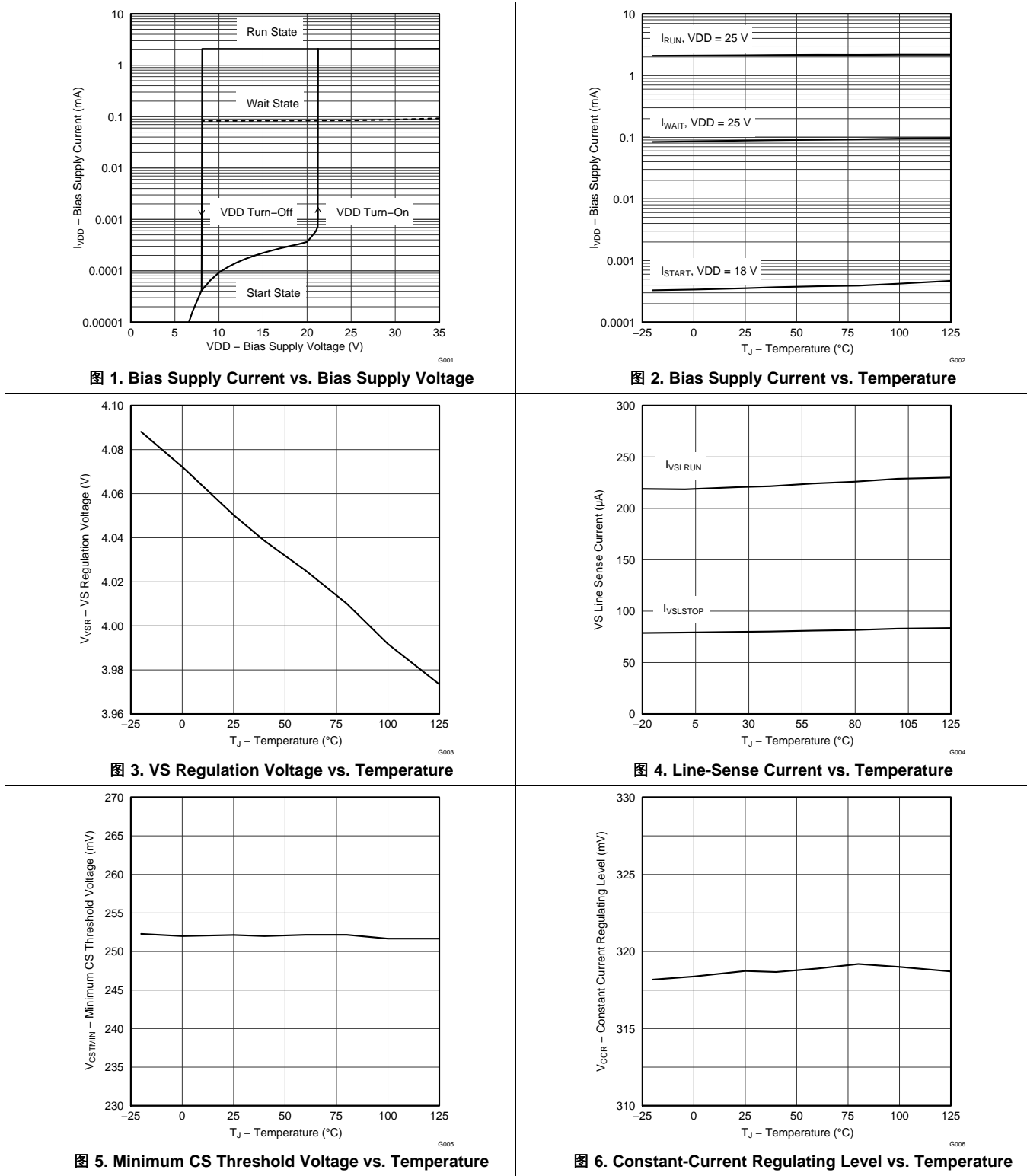
over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
$f_{SW(\text{max})}$	Maximum switching frequency	$V_{VS} = 3.7\text{ V}^{(1)}$	120	130	140	kHz
$f_{SW(\text{min})}$	Minimum switching frequency	$V_{VS} = 4.35\text{ V}^{(1)}$	875	1000	1100	Hz
$T_{ZTO}$	Zero-crossing timeout delay		1.80	2.10	2.55	$\mu\text{s}$

(1) These devices automatically vary the control frequency and current sense thresholds to improve EMI performance, these threshold voltages and frequency limits represent average levels.

### 6.7 Typical Characteristics

At VDD = 25 V, unless otherwise noted.



Typical Characteristics (接下页)

At VDD = 25 V, unless otherwise noted.

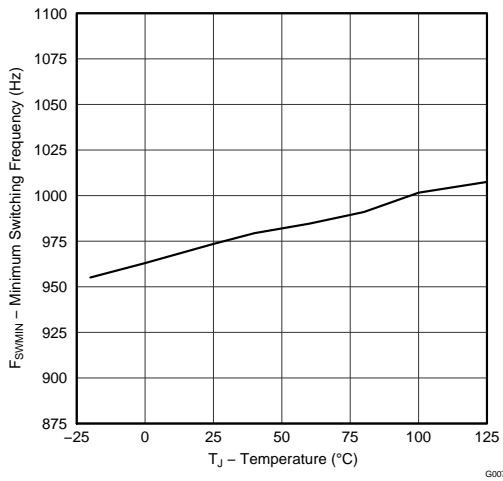
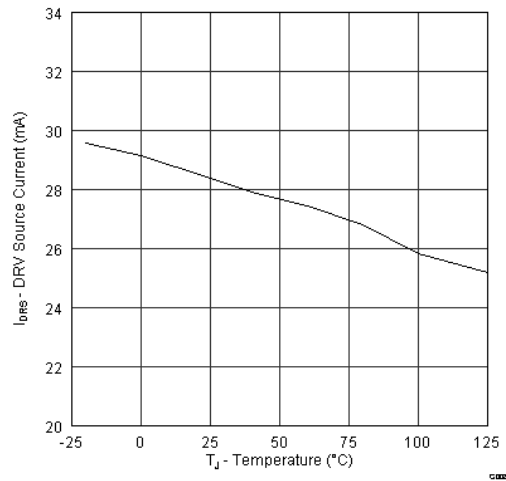


图 7. Minimum Switching Frequency vs. Temperature



V<sub>DRV</sub> = 8 V, V<sub>VDD</sub> = 9 V

图 8. DRV Source Current vs. Temperature

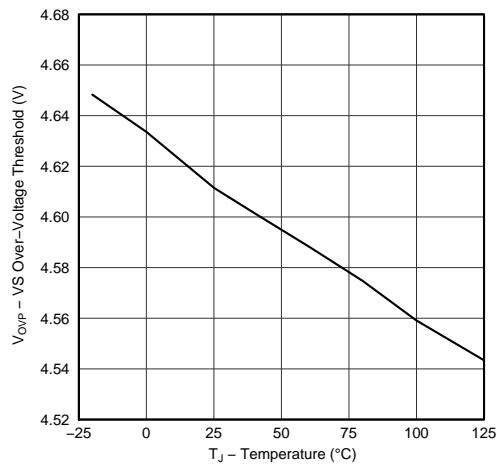


图 9. Overvoltage Threshold vs. Temperature



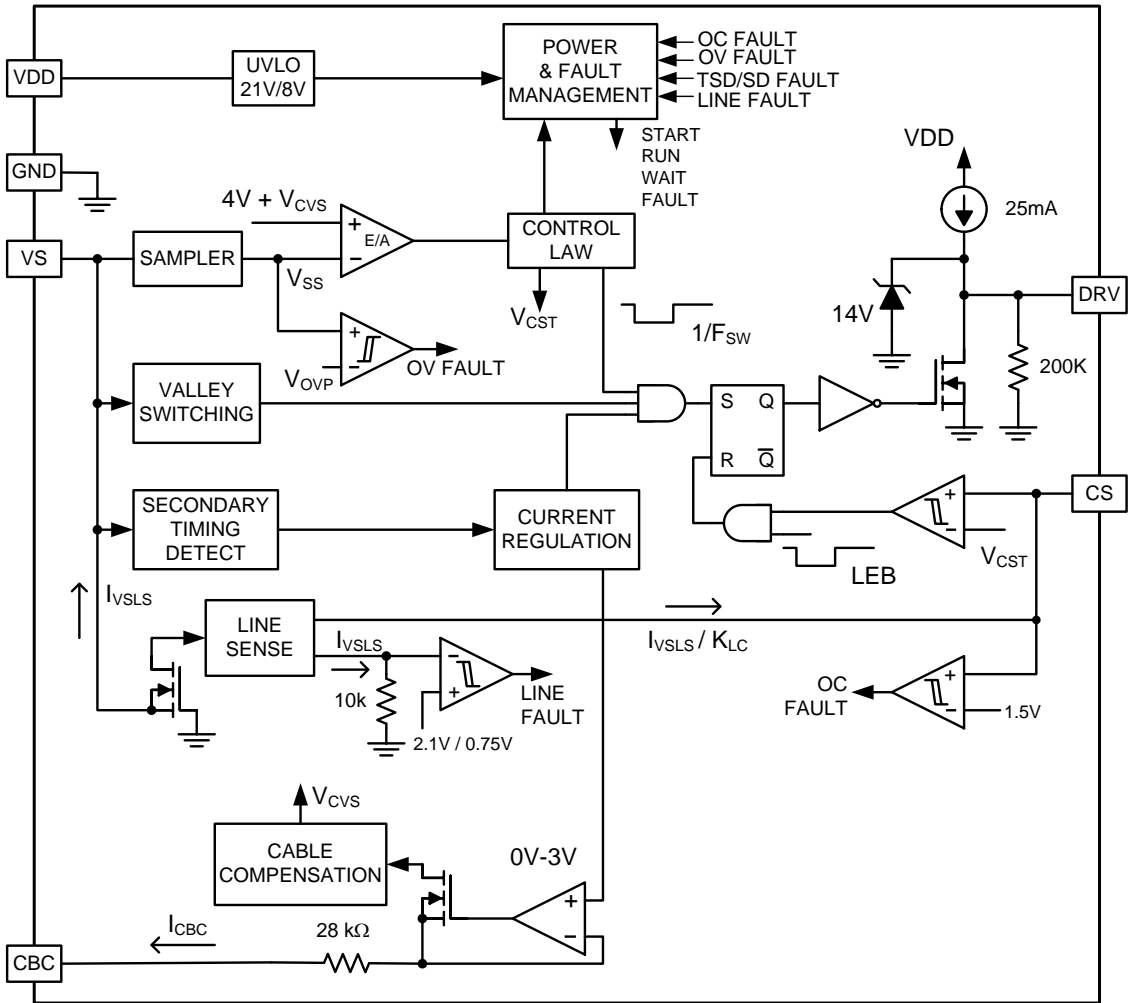
## 7 Detailed Description

### 7.1 Overview

The UCC28700-Q1 is a flyback power supply controller which provides accurate voltage and constant current regulation with primary-side feedback, eliminating the need for opto-coupler feedback circuits. The controller operates in discontinuous conduction mode with valley-switching to minimize switching losses. The modulation scheme is a combination of frequency and primary peak current modulation to provide high conversion efficiency across the load range. The control law provides a wide-dynamic operating range of output power to achieve the <30-mW stand-by power requirement.

Another feature beneficial to achieve low stand-by power without excessive start-up time is a wide operating VDD range to allow a high-value VDD start-up resistance and low-value VDD capacitance. During low-power operating ranges the device has power management features to reduce the device operating current at operating frequencies below 44 kHz. The UCC28700-Q1 controller includes features in the modulator to reduce the EMI peak energy of the fundamental switching frequency and harmonics. Accurate voltage and constant current regulation, fast dynamic response, and fault protection are achieved with primary-side control. A complete charger solution can be realized with a straightforward design process, low cost and low component count.

### 7.2 Functional Block Diagram



## 7.3 Feature Description

### 7.3.1 Detailed Pin Description

#### 7.3.1.1 VDD (Device Bias Voltage Supply)

The VDD pin is connected to a bypass capacitor to ground and a start-up resistance to the input bulk capacitor (+) terminal. The VDD turn-on UVLO threshold is 21 V and turn-off UVLO threshold is 8.1 V, with an available operating range up to 35 V. The USB charging specification requires the output current to operate in constant-current mode from 5 V to a minimum of 2 V; this is easily achieved with a nominal VDD of approximately 25 V. The additional VDD headroom up to 35 V allows for VDD to rise due to the leakage energy delivered to the VDD capacitor in high-load conditions. Also, the wide VDD range provides the advantage of selecting a relatively small VDD capacitor and high-value start-up resistance to minimize no-load stand-by power loss in the start-up resistor.

#### 7.3.1.2 GND (Ground)

This is a single ground reference external to the device for the gate drive current and analog signal reference. Place the VDD bypass capacitor close to GND and VDD with short traces to minimize noise on the VS and CS signal pins.

#### 7.3.1.3 VS (Voltage-Sense)

The VS pin is connected to a resistor divider from the auxiliary winding to ground. The output-voltage feedback information is sampled at the end of the transformer secondary current demagnetization time to provide an accurate representation of the output voltage. Timing information to achieve valley-switching and to control the duty cycle of the secondary transformer current is determined by the waveform on the VS pin. Avoid placing a filter capacitor on this input which would interfere with accurate sensing of this waveform.

The VS pin also senses the bulk capacitor voltage to provide for AC-input run and stop thresholds, and to compensate the current-sense threshold across the AC-input range. This information is sensed during the MOSFET on-time. For the AC-input run/stop function, the run threshold on VS is 220  $\mu$ A and the stop threshold is 80  $\mu$ A. The values for the auxiliary voltage divider upper-resistor  $R_{S1}$  and lower-resistor  $R_{S2}$  can be determined by the equations below.

$$R_{S1} = \frac{V_{IN(run)} \times \sqrt{2}}{N_{PA} \times I_{VSL(run)}}$$

where

- $N_{PA}$  is the transformer primary-to-auxiliary turns ratio,
- $V_{IN(run)}$  is the AC RMS voltage to enable turn-on of the controller (run),
- $I_{VSL(run)}$  is the run-threshold for the current pulled out of the VS pin during the MOSFET on-time. (see the [Electrical Characteristics](#) table)

(1)

$$R_{S2} = \frac{R_{S1} \times V_{VSR}}{N_{AS} \times (V_{OCV} + V_F) - V_{VSR}}$$

where

- $V_{OCV}$  is the converter regulated output voltage,
- $V_F$  is the output rectifier forward drop at near-zero current,
- $N_{AS}$  is the transformer auxiliary to secondary turns ratio,
- $R_{S1}$  is the VS divider high-side resistance,
- $V_{VSR}$  is the CV regulating level at the VS input (see the [Electrical Characteristics](#) table).

(2)

## Feature Description (接下页)

### 7.3.1.4 DRV (Gate Drive)

The DRV pin is connected to the MOSFET gate pin, usually through a series resistor. The gate driver provides a gate-drive signal limited to 14 V. The turn-on characteristic of the driver is a 25-mA current source which limits the turn-on dv/dt of the MOSFET drain and reduces the leading-edge current spike, but still provides gate-drive current to overcome the Miller plateau. The gate-drive turn-off current is determined by the low-side driver  $R_{DS(on)}$  and any external gate-drive resistance. The user can reduce the turn-off MOSFET drain dv/dt by adding external gate resistance.

### 7.3.1.5 CS (Current Sense)

The current-sense pin is connected through a series resistor ( $R_{LC}$ ) to the current-sense resistor ( $R_{CS}$ ). The current-sense threshold is 0.75 V for  $I_{PP(max)}$  and 0.25 V for  $I_{PP(min)}$ . The series resistor  $R_{LC}$  provides the function of feed-forward line compensation to eliminate change in  $I_{PP}$  due to change in di/dt and the propagation delay of the internal comparator and MOSFET turn-off time. There is an internal leading-edge blanking time of 235 ns to eliminate sensitivity to the MOSFET turn-on current spike. It should not be necessary to place a bypass capacitor on the CS pin. The value of  $R_{CS}$  is determined by the target output current in constant-current (CC) regulation. The values of  $R_{CS}$  and  $R_{LC}$  can be determined by the equations below. The term  $\eta_{XFMR}$  is intended to account for the energy stored in the transformer but not delivered to the secondary. This includes transformer resistance and core loss, bias power, and primary-to-secondary leakage ratio.

**Example:** With a transformer core and winding loss of 5%, primary-to-secondary leakage inductance of 3.5%, and bias power to output power ratio of 1.5%. The  $\eta_{XFMR}$  value is approximately:  $1 - 0.05 - 0.035 - 0.015 = 0.9$ .

$$R_{CS} = \frac{V_{CCR} \times N_{PS}}{2I_{OCC}} \times \eta_{XFMR}$$

where

- $V_{CCR}$  is a current regulation constant (see the [Electrical Characteristics](#) table),
- $N_{PS}$  is the transformer primary-to-secondary turns ratio (a ratio of 13 to 15 is recommended for 5-V output),
- $I_{OCC}$  is the target output current in constant-current regulation,
- $\eta_{XFMR}$  is the transformer efficiency. (3)

$$R_{LC} = \frac{K_{LC} \times R_{S1} \times R_{CS} \times T_D \times N_{PA}}{L_P}$$

where

- $R_{S1}$  is the VS pin high-side resistor value,
- $R_{CS}$  is the current-sense resistor value,
- $T_D$  is the current-sense delay including MOSFET turn-off delay, add ~50 ns to MOSFET delay,
- $N_{PA}$  is the transformer primary-to-auxiliary turns ratio,
- $L_P$  is the transformer primary inductance,
- $K_{LC}$  is a current-scaling constant (see the [Electrical Characteristics](#) table). (4)

## Feature Description (接下页)

### 7.3.1.6 CBC (Cable Compensation)

The cable compensation pin is connected to a resistor to ground to program the amount of output voltage compensation to offset cable resistance. The cable compensation block provides a 0-V to 3-V voltage level on the CBC pin corresponding to 0 to  $I_{OCC}$  output current. The resistance selected on the CBC pin programs a current mirror that is summed into the VS feedback divider therefore increasing the output voltage as  $I_{OUT}$  increases. There is an internal series resistance of 28 k $\Omega$  to the CBC pin which sets a maximum cable compensation of a 5-V output to 400 mV when CBC is shorted to ground. The CBC resistance value can be determined by the equation below.

$$R_{CBC} = \frac{V_{CBC(max)} \times 3 \text{ k}\Omega \times (V_{OCV} + V_F)}{V_{VSR} \times V_{OCBC}} - 28 \text{ k}\Omega$$

where

- $V_O$  is the output voltage,
- $V_F$  is the diode forward voltage,
- $V_{OCBC}$  is the target cable compensation voltage at the output terminals,
- $V_{CBC(max)}$  is the maximum voltage at the cable compensation pin at the maximum converter output current (see the [Electrical Characteristics](#) table),
- $V_{VSR}$  is the CV regulating level at the VS input (see the [Electrical Characteristics](#) table). (5)

### 7.3.2 Fault Protection

There is comprehensive fault protection incorporated into the UCC28700-Q1. Protection functions include:

- Output overvoltage
- Input undervoltage
- Internal overtemperature
- Primary overcurrent fault
- CS pin fault
- VS pin fault

A UVLO reset and restart sequence applies for all fault protection events.

The output over-voltage function is determined by the voltage feedback on the VS pin. If the voltage sample on VS exceeds 115% of the nominal  $V_{OUT}$ , the device stops switching and keeps the internal circuitry enabled to discharge the VDD capacitor to the UVLO turn-off threshold. After that, the device returns to the start state and a start-up sequence ensues.

The UCC28700-Q1 always operates with cycle-by-cycle primary peak current control. The normal operating range of the CS pin is 0.75 V to 0.25 V. There is additional protection if the CS pin reaches 1.5 V. This results in a UVLO reset and restart sequence. There is no leading-edge blanking on the 1.5-V threshold on CS.

The line input run and stop thresholds are determined by current information at the VS pin during the MOSFET on-time. While the VS pin is clamped close to GND during the MOSFET on-time, the current through  $R_{S1}$  is monitored to determine a sample of the bulk capacitor voltage. A wide separation of run and stop thresholds allows clean start-up and shut-down of the power supply with the line voltage. The run current threshold is 220  $\mu$ A and the stop current threshold is 80  $\mu$ A.

The internal overtemperature protection threshold is 165°C. If the junction temperature reaches this threshold the device initiates a UVLO reset cycle. If the temperature is still high at the end of the UVLO cycle, the protection cycle repeats.

Protection is included in the event of component failures on the VS pin. If complete loss of feedback information on the VS pin occurs, the controller stops switching and restarts.

## 7.4 Device Functional Modes

### 7.4.1 Primary-Side Voltage Regulation

Figure 10 shows a simplified flyback converter with the main voltage regulation blocks of the device shown. The power train operation is the same as any DCM flyback circuit but accurate output voltage and current sensing is the key to primary-side control.

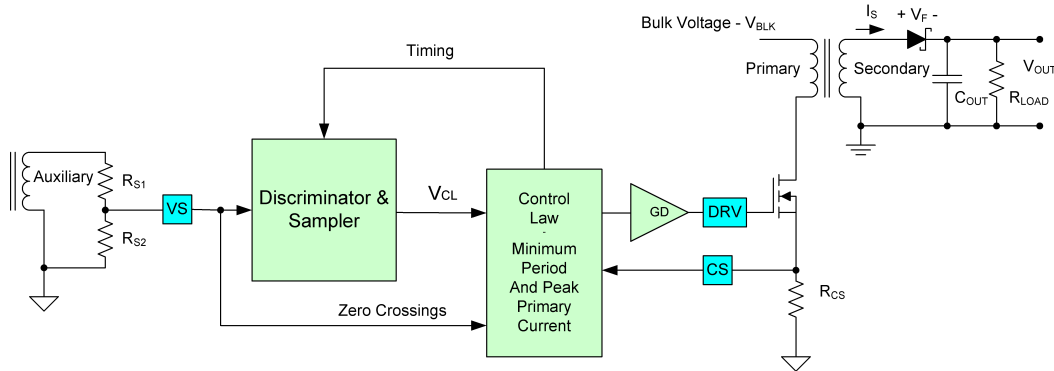


Figure 10. Simplified Flyback Converter (with the main voltage regulation blocks)

In primary-side control, the output voltage is sensed on the auxiliary winding during the transfer of transformer energy to the secondary. As shown in Figure 11 it is clear there is a down slope representing a decreasing total rectifier  $V_F$  and resistance voltage drop ( $I_S R_S$ ) as the secondary current decreases to zero. To achieve an accurate representation of the secondary output voltage on the auxiliary winding, the discriminator reliably blocks the leakage inductance reset and ringing, continuously samples the auxiliary voltage during the down slope after the ringing is diminished, and captures the error signal at the time the secondary winding reaches zero current. The internal reference on VS is 4.05 V; the resistor divider is selected as outlined in the VS pin description.

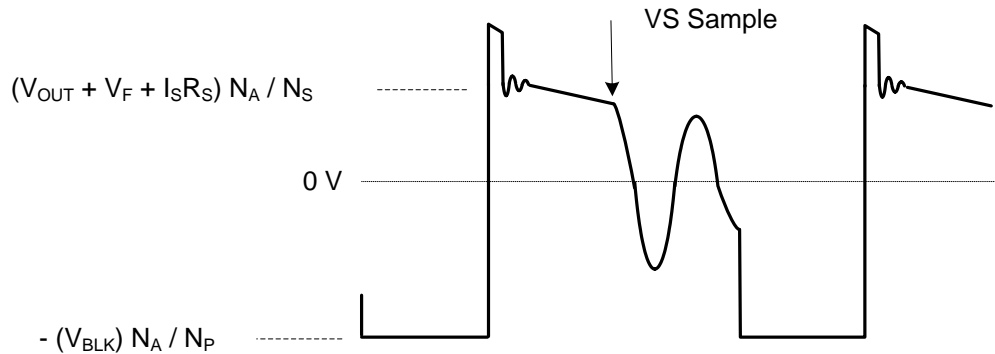


Figure 11. Auxiliary Winding Voltage

The UCC28700-Q1 VS signal sampler includes signal discrimination methods to ensure an accurate sample of the output voltage from the auxiliary winding. There are however some details of the auxiliary winding signal to ensure reliable operation, specifically the reset time of the leakage inductance and the duration of any subsequent leakage inductance ring. Refer to Figure 12 for a detailed illustration of waveform criteria to ensure a reliable sample on the VS pin. The first detail to examine is the duration of the leakage inductance reset pedestal,  $T_{LK\_RESET}$  in Figure 12. Because this can mimic the waveform of the secondary current decay, followed by a sharp downslope, it is important to keep the leakage reset time less than 500 ns for  $I_{PRI}$  minimum, and less than 1.5  $\mu$ s for  $I_{PRI}$  maximum. The second detail is the amplitude of ringing on the  $V_{AUX}$  waveform following  $T_{LK\_RESET}$ . The peak-to-peak voltage at the VS pin should be less than approximately 100 mV<sub>p-p</sub> at least 200 ns before the end of the demagnetization time,  $t_{DM}$ . If there is a concern with excessive ringing, it usually occurs during light or no-load conditions, when  $t_{DM}$  is at the minimum. The tolerable ripple on VS is scaled up to the auxiliary winding voltage by  $R_{S1}$  and  $R_{S2}$ , and is equal to 100 mV x  $(R_{S1} + R_{S2}) / R_{S2}$ .

Device Functional Modes (接下页)

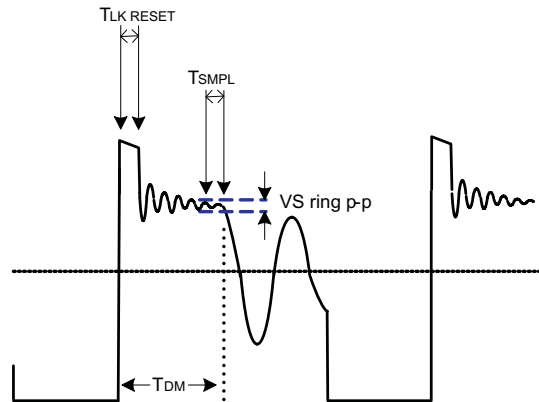


图 12. Auxiliary Waveform Details

During voltage regulation, the controller operates in frequency modulation mode and amplitude modulation mode as illustrated in 图 13 below. The internal operating frequency limits of the device are 130 kHz maximum and 1 kHz minimum. The transformer primary inductance and primary peak current chosen sets the maximum operating frequency of the converter. The output preload resistor and efficiency at low power determines the converter minimum operating frequency. There is no stability compensation required for the UCC28700-Q1 controller.

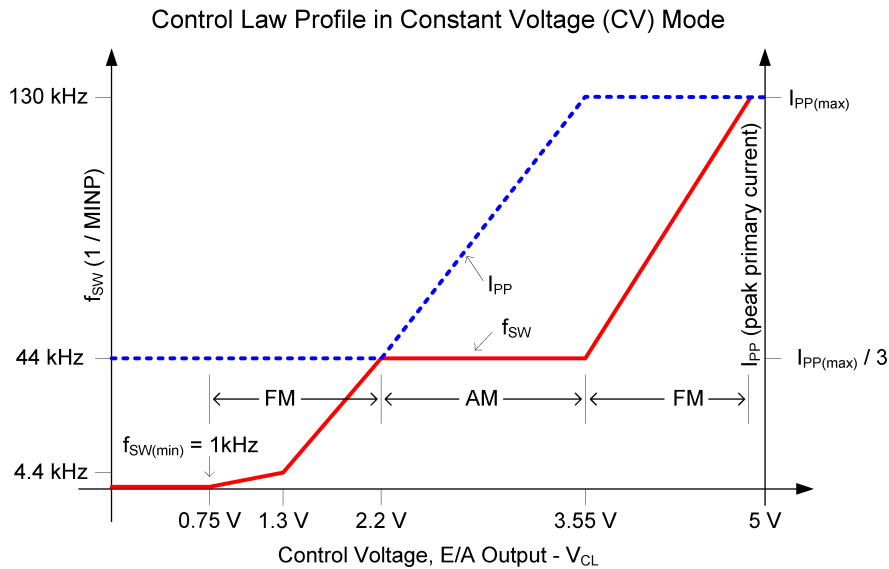


图 13. Frequency and Amplitude Modulation Modes (during voltage regulation)

## Device Functional Modes (接下页)

### 7.4.2 Primary-Side Current Regulation

Timing information at the VS pin and current information at the CS pin allow accurate regulation of the secondary average current. The control law dictates that as power is increased in CV regulation and approaching CC regulation the primary-peak current is at  $I_{PP(max)}$ . Referring to 图 14 below, the primary-peak current, turns ratio, secondary demagnetization time ( $t_{DM}$ ), and switching period ( $T_{SW}$ ) determine the secondary average output current. Ignoring leakage inductance effects, the average output current is given by 公式 6. When the average output current reaches the regulation reference in the current control block, the controller operates in frequency modulation mode to control the output current at any output voltage at or below the voltage regulation target as long as the auxiliary winding can keep VDD above the UVLO turn-off threshold.

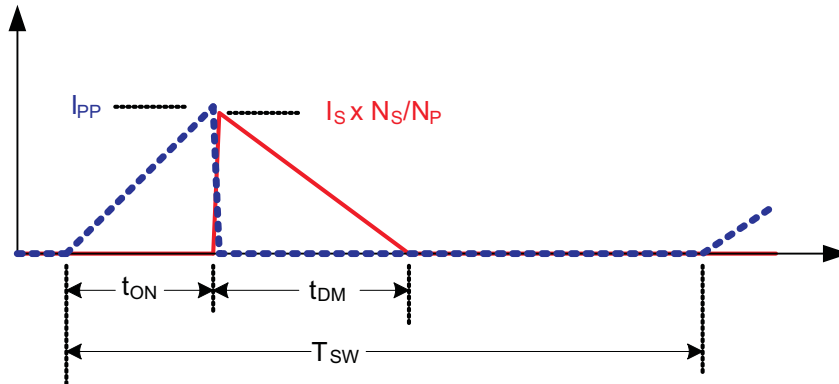


图 14. Transformer Currents

$$I_{OUT} = \frac{I_{PP}}{2} \times \frac{N_P}{N_S} \times \frac{t_{DM}}{T_{SW}} \tag{6}$$

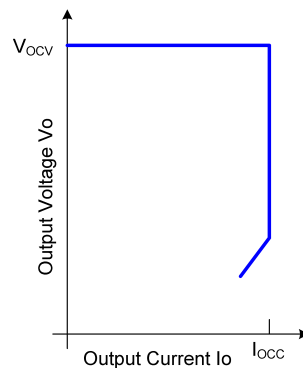


图 15. Typical Target Output V-I Characteristic

## Device Functional Modes (接下页)

### 7.4.3 Valley-Switching

The UCC28700-Q1 utilizes valley-switching to reduce switching losses in the MOSFET, to reduce induced-EMI, and to minimize the turn-on current spike at the sense resistor. The controller operates in valley-switching in all load conditions unless the  $V_{DS}$  ringing has diminished.

Referring to 图 16 below, the UCC28700-Q1 operates in a valley-skipping mode in most load conditions to maintain an accurate voltage or current regulation point and still switch on the lowest available  $V_{DS}$  voltage.

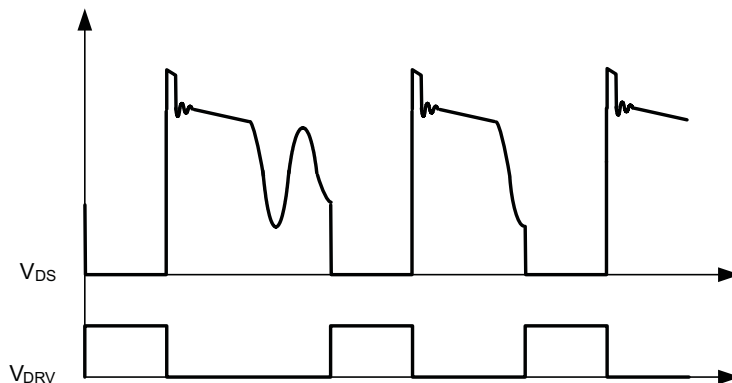


图 16. Valley-Skipping Mode

### 7.4.4 Start-Up Operation

Upon application of input voltage to the converter, the start-up resistor connected to VDD from the bulk capacitor voltage ( $V_{BLK}$ ) charges the VDD capacitor. During charging of the VDD capacitor the device bias supply current is less than  $1.5 \mu\text{A}$ . When VDD reaches the 21-V UVLO turn-on threshold, the controller is enabled and the converter starts switching. The initial three cycles are limited to  $I_{PP(\text{min})}$ . This allows sensing any initial input or output faults with minimal power delivery. After the initial three cycles at minimum  $I_{PP(\text{min})}$ , the controller responds to the condition dictated by the control law. The converter remains in discontinuous mode during charging of the output capacitor(s), maintaining a constant output current until the output voltage is in regulation.



## 8 Applications and Implementation

注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

### 8.1 Application Information

The UCC28700-Q1 flyback power supply controller provides constant voltage (CV) and constant current (CC) output regulation to help meet USB-compliant adaptors and charger requirements. These devices use the information obtained from auxiliary winding sensing (VS) to control the output voltage and do not require optocoupler/TL431 feedback circuitry. Not requiring optocoupler feedback reduces the component count and makes the design more cost effective.

### 8.2 Typical Application

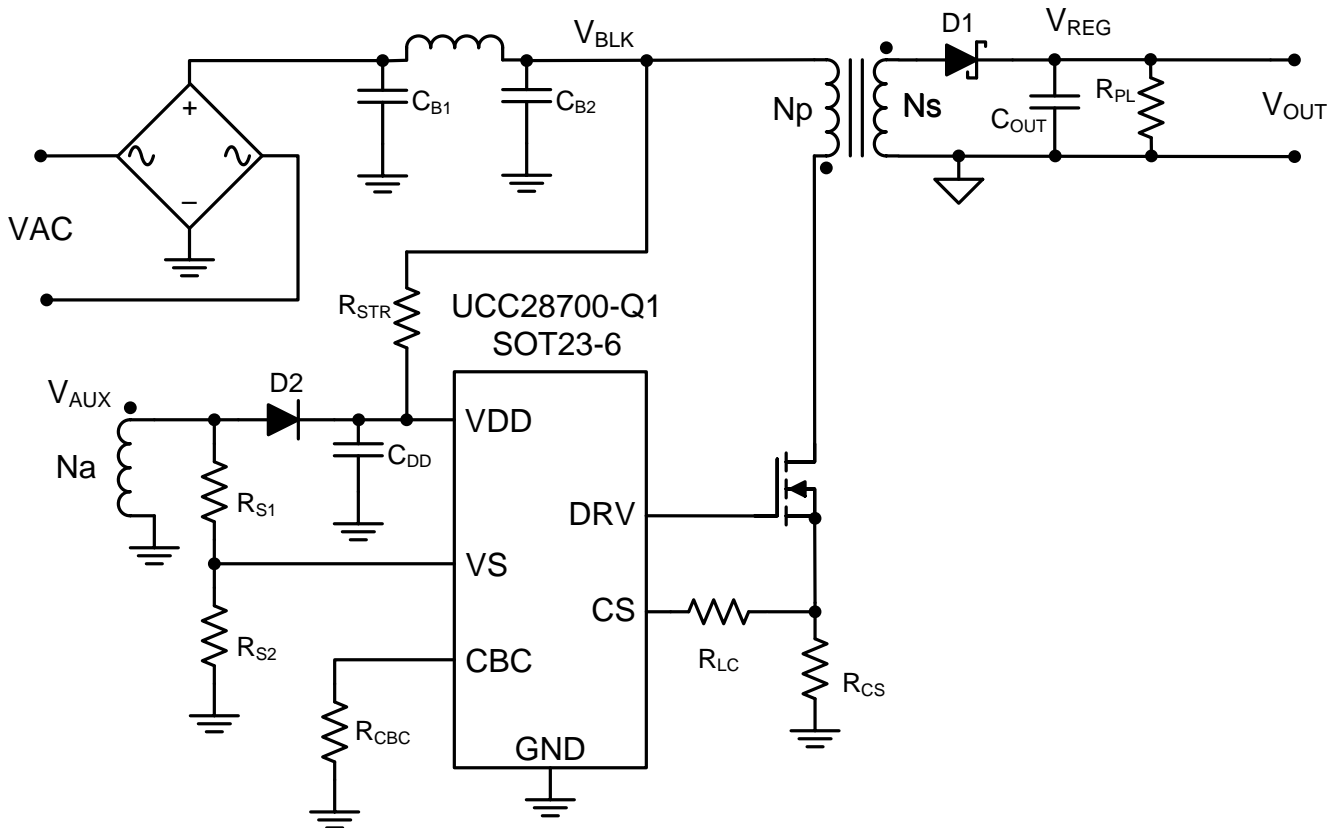


图 17. Typical Application Circuit

**Typical Application (接下页)**
**8.2.1 Design Requirements**
**表 1. Design Parameters**

PARAMETER	SYMBOL	NOTES AND CONDITIONS	MIN	NOM	MAX	UNIT
<b>INPUT CHARACTERISTICS</b>						
Input Voltage	$V_{IN}$		100	115/230	240	V
Line Frequency	$f_{LINE}$		47	50/60	64	Hz
No Load Input Power	$P_{SB\_CONV}$	$V_{IN} = \text{Nom}, I_O = 0 \text{ A}$			30	mW
Brownout Voltage	$V_{IN(RUN)}$	$I_O = \text{Nom}$		70		V
<b>OUTPUT CHARACTERISTICS</b>						
Output Voltage	$V_O$	$V_{IN} = \text{Nom}, I_O = \text{Nom}$	4.75	5	5.25	V
Output Voltage Ripple	$V_{RIPPLE}$	$V_{IN} = \text{Nom}, I_O = \text{Max}$			0.1	V
Output Current	$I_O$	$V_{IN} = \text{Min to Max}$		1	1.05	A
Output OVP	$V_{OVP}$	$I_{OUT} = \text{Min to Max}$		5.75		V
Transient Response						
Load Step ( $V_O = 4.1 \text{ V to } 6 \text{ V}$ )	$V_{O\Delta}$	(0.1 A to 0.6 A) or (0.6 A to 0.1 A) $V_{O\Delta} = 0.9 \text{ V}$ for $C_{OUT}$ calculation in applications section	4.1	5	6	V
<b>SYSTEMS CHARACTERISTICS</b>						
Switching Frequency					105	kHz
Full Load Efficiency (115/230 V RMS Input)	$\eta$	$I_O = 1 \text{ A}$	74%		76%	

## 8.2.2 Detailed Design Procedure

This procedure outlines the steps to design a constant-voltage, constant-current flyback converter using the UCC28700-Q1 controller. Please refer to the [图 17](#) for circuit details and section [器件命名规则](#) for variable definitions used in the applications equations below.

### 8.2.2.1 Transformer Parameter Verification

The transformer turns ratio selected affects the MOSFET  $V_{DS}$  and secondary rectifier reverse voltage so these should be reviewed. The UCC28700-Q1 controller requires a minimum on time of the MOSFET ( $T_{ON}$ ) and minimum  $D_{MAG}$  time ( $T_{DMAG}$ ) of the secondary rectifier in the high line, minimum load condition. The selection of  $F_{MAX}$ ,  $L_P$  and  $R_{CS}$  affects the minimum  $T_{ON}$  and  $T_{DMAG}$ .

The secondary rectifier and MOSFET voltage stress can be determined by the equations below.

$$V_{REV} = \frac{V_{IN(max)} \times \sqrt{2}}{N_{PS}} + V_{OCV} + V_{OCBC} \quad (7)$$

For the MOSFET  $V_{DS}$  voltage stress, an estimated leakage inductance voltage spike ( $V_{LK}$ ) needs to be included.

$$V_{DSPK} = (V_{IN(max)} \times \sqrt{2}) + (V_{OCV} + V_F + V_{OCBC}) \times N_{PS} + V_{LK} \quad (8)$$

The following equations are used to determine if the minimum  $T_{ON}$  target of 300 ns and minimum  $T_{DMAG}$  target of 1.1  $\mu$ s is achieved.

$$T_{ON(min)} = \frac{L_P}{V_{IN(max)} \times \sqrt{2}} \times \frac{I_{PP(max)} \times V_{CST(min)}}{V_{CST(max)}} \quad (9)$$

$$T_{DMAG(min)} = \frac{T_{ON(min)} \times V_{IN(max)} \times \sqrt{2}}{N_{PS} \times (V_{OCV} + V_F)} \quad (10)$$

### 8.2.2.2 Output Capacitance

The output capacitance value is typically determined by the transient response requirement from no-load. For example, in some USB charger applications there is a requirement to maintain a minimum  $V_O$  of 4.1 V with a load-step transient of 0 mA to 500 mA. The equation below assumes that the switching frequency can be at the UCC28700-Q1 minimum of  $f_{SW(min)}$ .

$$C_{OUT} = \frac{I_{TRAN} \left( \frac{1}{f_{SW(min)}} + 150 \mu s \right)}{V_{O\Delta}} \quad (11)$$

Another consideration of the output capacitor(s) is the ripple voltage requirement which is reviewed based on secondary peak current and ESR. A margin of 20% is added to the capacitor ESR requirement in the equation below.

$$R_{ESR} = \frac{V_{RIPPLE} \times 0.8}{I_{PP(max)} \times N_{PS}} \quad (12)$$

### 8.2.2.3 VDD Capacitance, $C_{DD}$

The capacitance on VDD needs to supply the device operating current until the output of the converter reaches the target minimum operating voltage in constant-current regulation. At this time the auxiliary winding can sustain the voltage to the UCC28700-Q1. The total output current available to the load and to charge the output capacitors is the constant-current regulation target. The equation below assumes the output current of the flyback is available to charge the output capacitance until the minimum output voltage is achieved. There is an estimated 1 mA of gate-drive current in the equation and 1 V of margin added to VDD.

$$C_{DD} = \frac{(I_{RUN} + 1\text{mA}) \times \frac{C_{OUT} \times V_{OCC}}{I_O}}{(V_{DD(on)} - V_{DD(off)}) - 1\text{V}} \quad (13)$$

### 8.2.2.4 VDD Start-Up Resistance, $R_{STR}$

Once the VDD capacitance is known, the start-up resistance from  $V_{BULK}$  to achieve the turn-on time target can be determined.

$$R_{STR} = \frac{\sqrt{2} \times V_{IN(min)}}{I_{START} + \frac{V_{DD(on)} \times C_{DD}}{T_{STR}}} \quad (14)$$

### 8.2.2.5 VS Resistor Divider, Line Compensation, and Cable Compensation

The VS divider resistors determine the output voltage regulation point of the flyback converter, also the high-side divider resistor ( $R_{S1}$ ) determines the line voltage at which the controller enables continuous DRV operation.  $R_{S1}$  is initially determined based on transformer auxiliary to primary turns ratio and desired input voltage operating threshold.

$$R_{S1} = \frac{V_{IN(run)} \times \sqrt{2}}{N_{PA} \times I_{VSL(run)}} \quad (15)$$

The low-side VS pin resistor is selected based on desired  $V_O$  regulation voltage.

$$R_{S2} = \frac{R_{S1} \times V_{VSR}}{N_{AS} \times (V_{OCV} + V_F) - V_{VSR}} \quad (16)$$

The UCC28700-Q1 can maintain tight constant-current regulation over input line by utilizing the line compensation feature. The line compensation resistor ( $R_{LC}$ ) value is determined by current flowing in  $R_{S1}$  and expected gate drive and MOSFET turn-off delay. Assume a 50-ns internal delay in the UCC28700-Q1.

$$R_{LC} = \frac{K_{LC} \times R_{S1} \times R_{CS} \times T_D \times N_{PA}}{L_P} \quad (17)$$

On the UCC28700-Q1 which has adjustable cable compensation, the resistance for the desired compensation level at the output terminals can be determined using the equation below.

$$R_{CBC} = \frac{V_{CBC(max)} \times 3\text{k}\Omega \times (V_{OCV} + V_F)}{V_{VSR} \times V_{OCBC}} - 28\text{k}\Omega \quad (18)$$

### 8.2.2.6 Input Bulk Capacitance and Minimum Bulk Voltage

Determine the minimum voltage on the input capacitance,  $C_{B1}$  and  $C_{B2}$  total, in order to determine the maximum  $N_p$  to  $N_s$  turns ratio of the transformer. The input power of the converter based on target full-load efficiency, minimum input RMS voltage, and minimum AC input frequency are used to determine the input capacitance requirement.

Maximum input power is determined based on  $V_{OCV}$ ,  $I_{OCC}$ , and the full-load efficiency target.

$$P_{IN} = \frac{V_{OCV} \times I_{OCC}}{\eta} \quad (19)$$

The below equation provides an accurate solution for input capacitance based on a target minimum bulk capacitor voltage. To target a given input capacitance value, iterate the minimum capacitor voltage to achieve the target capacitance.

$$C_{BULK} = \frac{2P_{IN} \times \left( 0.25 + \frac{1}{2\pi} \times \arcsin \left( \frac{V_{BULK(min)}}{\sqrt{2} \times V_{IN(min)}} \right) \right)}{\left( 2V_{IN(min)}^2 - V_{BULK(min)}^2 \right) \times f_{LINE}} \quad (20)$$

### 8.2.2.7 Transformer Turns Ratio, Inductance, Primary-Peak Current

The maximum primary-to-secondary turns ratio can be determined by the target maximum switching frequency at full load, the minimum input capacitor bulk voltage, and the estimated DCM quasi-resonant time.

Initially determine the maximum available total duty cycle of the on time and secondary conduction time based on target switching frequency and DCM resonant time. For DCM resonant time, assume 500 kHz if you do not have an estimate from previous designs. For the transition mode operation limit, the period required from the end of secondary current conduction to the first valley of the  $V_{DS}$  voltage is  $\frac{1}{2}$  of the DCM resonant period, or  $1 \mu\text{s}$  assuming 500-kHz resonant frequency.  $D_{MAX}$  can be determined using the equation below.

$$D_{MAX} = 1 - \left( \frac{T_R}{2} \times f_{MAX} \right) - D_{MAGCC} \quad (21)$$

Once  $D_{MAX}$  is known, the maximum turns ratio of the primary to secondary can be determined with the equation below.  $D_{MAGCC}$  is defined as the secondary diode conduction duty cycle during constant-current, CC, operation. It is set internally by the UCC28700-Q1 at 0.425. The total voltage on the secondary winding needs to be determined; which is the sum of  $V_{OCV}$ , the secondary rectifier  $V_F$ , and the cable compensation voltage ( $V_{OCBC}$ ). For the 5-V USB charger applications, a turns ratio range of 13 to 15 is typically used.

$$N_{PS(max)} = \frac{D_{MAX} \times V_{BULK(min)}}{D_{MAGCC} \times (V_{OCV} + V_F + V_{OCBC})} \quad (22)$$

Once an optimum turns ratio is determined from a detailed transformer design, use this ratio for the following parameters.

The UCC28700-Q1 controller constant-current regulation is achieved by maintaining a maximum  $D_{MAG}$  duty cycle of 0.425 at the maximum primary current setting. The transformer turns ratio and constant-current regulating voltage determine the current sense resistor for a target constant current.

Since not all of the energy stored in the transformer is transferred to the secondary, a transformer efficiency term is included. This efficiency number includes the core and winding losses, leakage inductance ratio, and bias power ratio to rated output power. For a 5-V, 1-A charger example, bias power of 1.5% is a good estimate. An overall transformer efficiency of 0.9 is a good estimate to include 3.5% leakage inductance, 5% core and winding loss, and 1.5% bias power.

$$R_{CS} = \frac{V_{CCR} \times N_{PS}}{2I_{OCC}} \times \eta_{XFMR} \quad (23)$$

The primary transformer inductance can be calculated using the standard energy storage equation for flyback transformers. Primary current, maximum switching frequency and output and transformer power losses are included in the equation below. Initially determine transformer primary current.

Primary current is simply the maximum current sense threshold divided by the current sense resistance.

$$I_{PP(max)} = \frac{V_{CST(max)}}{R_{CS}} \quad (24)$$

$$L_P = \frac{2(V_{OCV} + V_F + V_{OCBC}) \times I_{OCC}}{\eta_{XFMR} \times I_{PP(max)}^2 \times f_{MAX}} \quad (25)$$

The secondary winding to auxiliary winding transformer turns ratio ( $N_{AS}$ ) is determined by the lowest target operating output voltage in constant-current regulation and the VDD UVLO of the UCC28700-Q1. There is additional energy supplied to VDD from the transformer leakage inductance energy which allows a lower turns ratio to be used in many designs.

$$N_{AS} = \frac{V_{DD(off)} + V_{FA}}{V_{OCC} + V_F} \quad (26)$$

### 8.2.2.8 Standby Power Estimate

Assuming no-load standby power is a critical design parameter, determine estimated no-load power based on target converter maximum switching frequency and output power rating.

The following equation estimates the stand-by power of the converter.

$$P_{SB\_CONV} = \frac{P_{OUT} \times f_{MIN}}{\eta_{SB} \times K_{AM}^2 \times f_{MAX}} \quad (27)$$

For a typical USB charger application, the bias power during no-load is approximately 2.5 mW. This is based on 25-V VDD and 100-μA bias current. The output preload resistor can be estimated by  $V_{OCV}$  and the difference in the converter stand-by power and the bias power. The equation for output preload resistance accounts for bias power estimated at 2.5 mW.

$$R_{PL} = \frac{V_{OCV}^2}{P_{SB\_CONV} - 2.5 \text{ mW}} \quad (28)$$

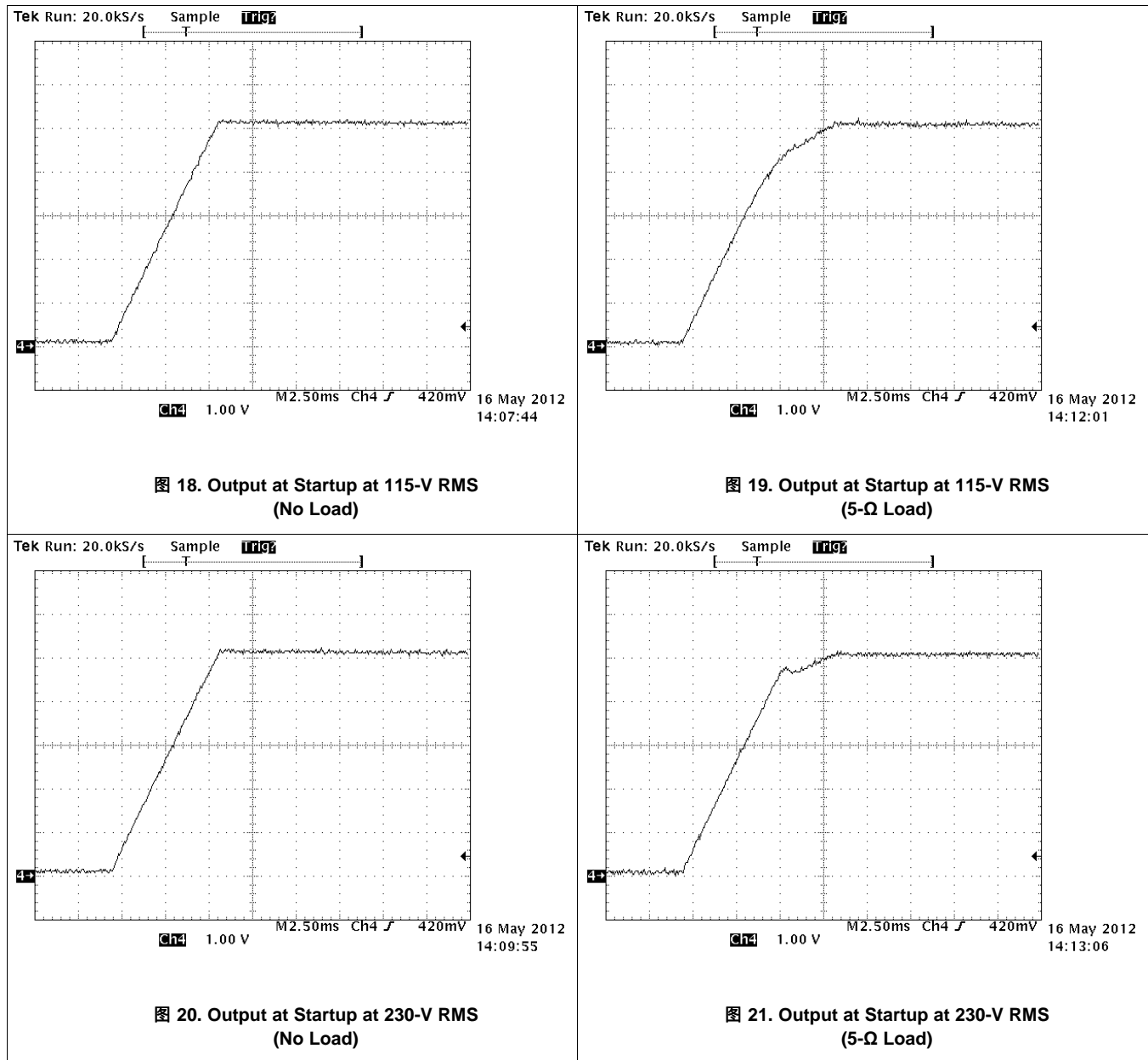
Typical start-up resistance values for  $R_{STR}$  range from 13 MΩ to 20 MΩ to achieve 1-s start-up time. The capacitor bulk voltage for the loss estimation is the highest voltage for the stand-by power measurement, typically 325  $V_{DC}$ .

$$P_{RSTR} = \frac{V_{BLK}^2}{R_{STR}} \quad (29)$$

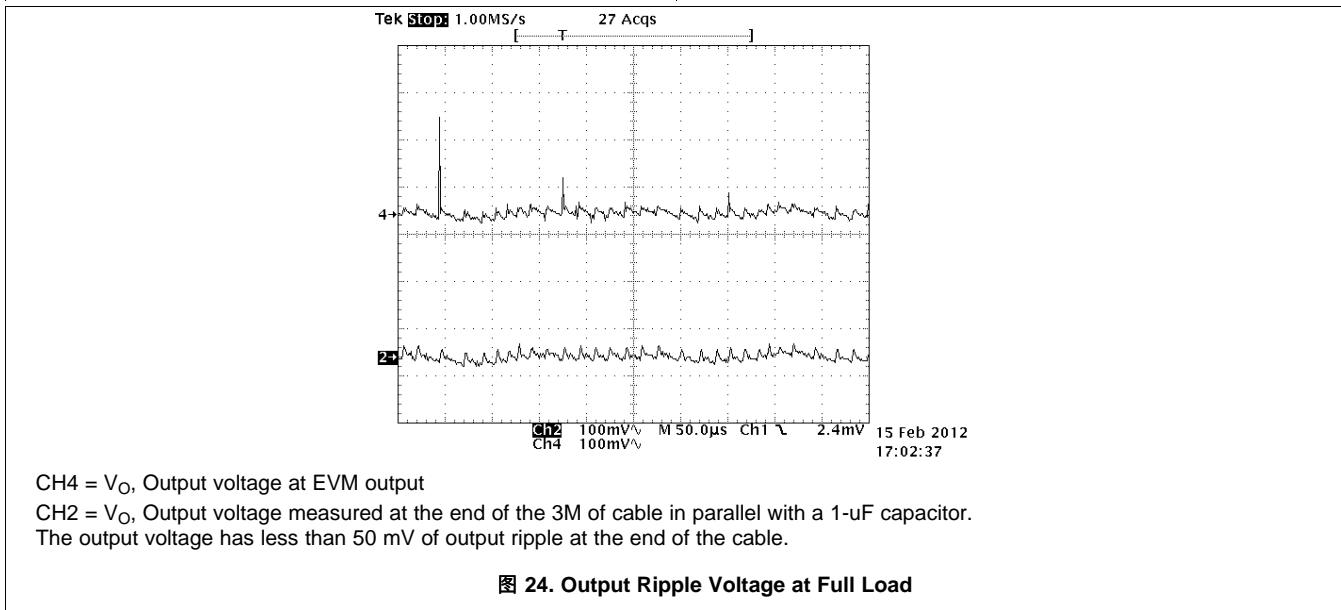
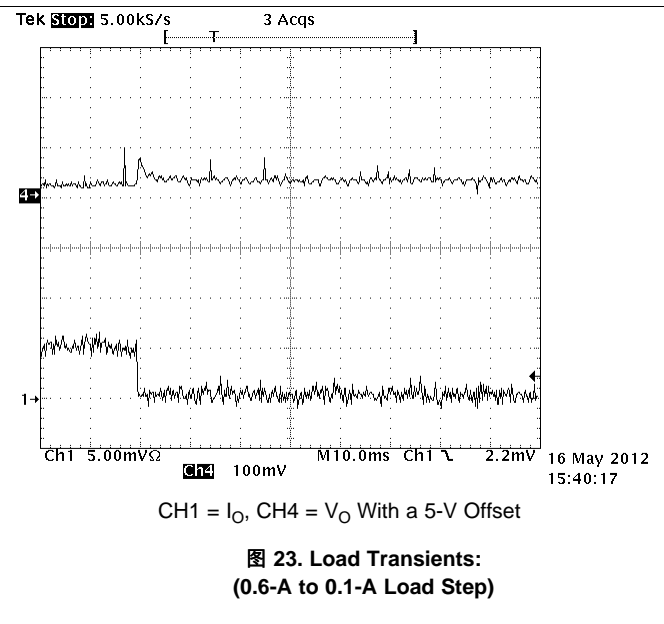
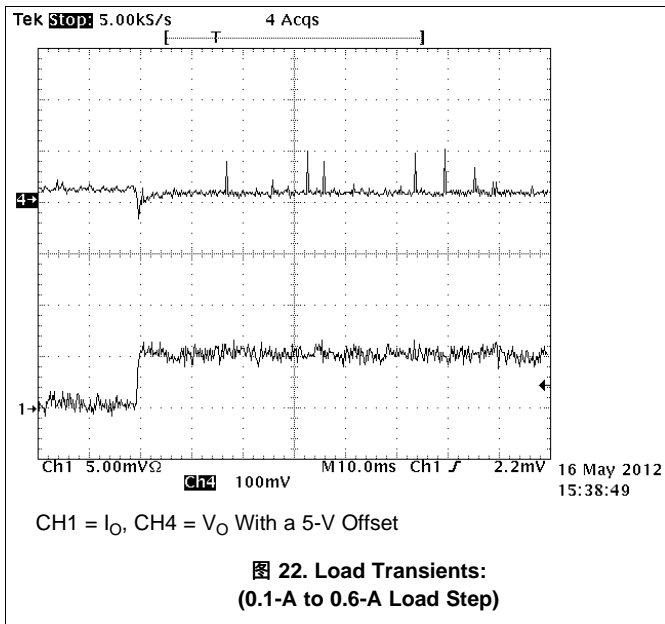
For the total stand-by power estimation add an estimated 2.5 mW for snubber loss to the start-up resistance and converter stand-by power loss.

$$P_{SB} = P_{SB\_CONV} + P_{RSTR} + 2.5 \text{ mW} \quad (30)$$

### 8.2.3 Application Curves







## 9 Power Supply Recommendations

The UCC28700-Q1 is intended for AC/DC converters with input voltage range of 85 V<sub>AC(rms)</sub> to 265 V<sub>AC(rms)</sub> using Flyback topology. It can be used in other applications and converter topologies with different input voltages. Be sure that all voltages and currents are within the recommended operating conditions and absolute maximum ratings of the device.

To maintain output current regulation over the entire input voltage range, design the converter to operate close to  $f_{MAX}$  when in full-load conditions.

To improve thermal performance increase the copper area connected to GND pins.

## 10 Layout

### 10.1 Layout Guidelines

- High frequency bypass Capacitor C7 should be placed across Pin 2 and 5 as close as you can get it to the pins.
- Resistor R15 and C7 form a low pass filter and the connection of R15 and C7 should be as close to the VDD pin as possible.
- C9 should be put as close to CS pin and R10 as possible. This forms a low pass filter with R10.
- The connection for C9 and R10 should be as close to the CS pin as possible.
- Please note that C9 may not be required in all designs. However, it is wise to put a place holder for it in your design.
- The VS pin controls the output voltage through the transformer turns ratio and the voltage divider of R7 and R9. Note the trace with between the R7, R9 and VS pin should be; as short as; possible to reduce/eliminate possible EMI coupling.
- Note the IC ground and power ground should meet at the bulk capacitor's (C4 and C5) return. Try to ensure that high frequency/high current from the power stage does not go through the signal ground.
  - The high frequency/high current path that you need to be cautious of on the primary is C4, C5 +, T1 (P1,P2), Q1d, Q1s, R13 to the return of C4 and C5.
- Try to keep all high current loops as short as possible.
- Keep all high current/high frequency traces away from or perpendicular to other traces in the design.
- Traces on the voltage clamp formed by D1, R1, D4 and C4 as short as possible.
- C4 return needs to be as close to the bulk capacitor supply as possible. This reduces the magnitude of dv/dt caused by large di/dt.
- Avoid mounting semiconductors under magnetics.



## 11 器件和文档支持

### 11.1 器件支持

#### 11.1.1 器件命名规则

##### 11.1.1.1 电容术语（以法拉为单位）

$C_{BULK}$	$C_{B1}$ 和 $C_{B2}$ 的总输入电容。
$C_{DD}$	VDD 引脚所需的最小电容。
$C_{OUT}$	所需的最小输出电容。

##### 11.1.1.2 占空比术语

$D_{MAGCC}$	CC 中二次侧二极管导通占空比, 0.425。
$D_{MAX}$	MOSFET 导通时间占空比。

##### 11.1.1.3 频率术语（以赫兹为单位）

$f_{LINE}$	最低线路频率。
$f_{MAX}$	转换器的最高目标满载开关频率。
$f_{MIN}$	转换器的最低开关频率, 在器件 $f_{SW(min)}$ 限值基础上增加 15% 的裕度。
$F_{SW(min)}$	最低开关频率 (见 <a href="#">Electrical Characteristics</a> 表)

##### 11.1.1.4 电流术语（以安培为单位）

$I_{OCC}$	转换器输出恒流目标。
$I_{PP(max)}$	变压器一次侧最大电流。
$I_{START}$	启动偏置电源电流 (见 <a href="#">Electrical Characteristics</a> 表)。
$I_{TRAN}$	所需的正负载阶跃电流。
$I_{VSL(run)}$	VS 引脚运行电流 (见 <a href="#">Electrical Characteristics</a> 表)。

##### 11.1.1.5 电流和电压调节术语

$K_{AM}$	一次侧峰峰值电流比 (见 <a href="#">Electrical Characteristics</a> 表)。
$K_{LC}$	电流调节常量 (见 <a href="#">Electrical Characteristics</a> 表)。

##### 11.1.1.6 变压器术语

$L_P$	变压器一次侧电感。
$N_{AS}$	变压器辅助绕组与二次侧绕组匝数比。
$N_{PA}$	变压器一次侧绕组与辅助绕组匝数比。
$N_{PS}$	变压器一次侧绕组与二次侧绕组匝数比。

##### 11.1.1.7 功率术语（以瓦特为单位）

$P_{IN}$	转换器最大输入功率。
$P_{OUT}$	转换器的满载输出功率。
$P_{RSTR}$	VDD 启动电阻功耗。
$P_{SB}$	总待机功耗。
$P_{SB\_CONV}$	$P_{SB}$ 与启动电阻和缓冲器功耗的差值。

**器件支持 (接下页)****11.1.1.8 电阻术语 (以  $\Omega$  为单位)**

<b>R<sub>CS</sub></b>	一次侧电流编程电阻
<b>R<sub>ESR</sub></b>	输出电容的总 ESR。
<b>R<sub>PL</sub></b>	转换器输出端的预载电阻。
<b>R<sub>S1</sub></b>	高侧 VS 引脚电阻。
<b>R<sub>S2</sub></b>	低侧 VS 引脚电阻。
<b>R<sub>STR</sub></b>	实现导通时间目标的最大启动电阻。
<b>R<sub>STR</sub></b>	V <sub>DD</sub> 启动电阻。

**11.1.1.9 时序术语 (以秒为单位)**

<b>T<sub>D</sub></b>	电流感测延迟 (包括 MOSFET 关断延迟)；在 MOSFET 延迟基础上增加 50ns。
<b>T<sub>DMAG(min)</sub></b>	二次侧整流器最短导通时间。
<b>T<sub>ON(min)</sub></b>	MOSFET 最短导通时间。
<b>T<sub>R</sub></b>	断续导通模式 (DCM) 期间的谐振频率。
<b>T<sub>STR</sub></b>	转换器启动时间要求。

**器件支持 (接下页)**
**11.1.1.10 电压术语 (以伏特为单位)**

<b>V<sub>BLK</sub></b>	用于待机功耗测量的大容量电容最高电压。
<b>V<sub>BULK(min)</sub></b>	满功率条件下 C <sub>B1</sub> 和 C <sub>B2</sub> 的最低电压。
<b>V<sub>OCBC</sub></b>	输出引脚的目标电缆补偿电压。
<b>V<sub>CBC(max)</sub></b>	最大转换器输出电流条件下 CBC 引脚的最大电压 (见 <a href="#">Electrical Characteristics</a> 表)。
<b>V<sub>CCR</sub></b>	恒流调节电压 (见 <a href="#">Electrical Characteristics</a> 表)。
<b>V<sub>CST(max)</sub></b>	CS 引脚的最大电流感测阈值 (见 <a href="#">Electrical Characteristics</a> 表)。
<b>V<sub>CST(min)</sub></b>	CS 引脚的最小电流感测阈值 (见 <a href="#">Electrical Characteristics</a> 表)。
<b>V<sub>DD(off)</sub></b>	UVLO 关断电压 (见 <a href="#">Electrical Characteristics</a> 表)。
<b>V<sub>DD(on)</sub></b>	UVLO 导通电压 (见 <a href="#">Electrical Characteristics</a> 表)。
<b>V<sub>OA</sub></b>	负载阶跃瞬态期间允许的输出压降。
<b>V<sub>DSPK</sub></b>	高压线条件下的 MOSFET 漏源电压峰值。
<b>V<sub>F</sub></b>	电流接近零时的二次侧整流器正向压降。
<b>V<sub>FA</sub></b>	辅助整流器正向压降。
<b>V<sub>LK</sub></b>	估计的漏感能量复位电压。
<b>V<sub>OCV</sub></b>	经稳压的转换器输出电压。
<b>V<sub>OCC</sub></b>	恒流稳压条件下的最低目标转换器输出电压。
<b>V<sub>REV</sub></b>	二次侧整流器的峰值反向电压。
<b>V<sub>RIPPLE</sub></b>	满载条件下的输出峰峰值纹波电压。
<b>V<sub>VSR</sub></b>	VS 输入端的 CV 调节电平 (见 <a href="#">Electrical Characteristics</a> 表)。

**11.1.1.11 交流电压术语 (以 V<sub>RMS</sub> 为单位)**

<b>V<sub>IN(max)</sub></b>	转换器的最大输入电压。
<b>V<sub>IN(min)</sub></b>	转换器的最小输入电压。
<b>V<sub>IN(run)</sub></b>	转换器输入启动 (运行) 电压。

**11.1.1.12 效率术语**

<b>η<sub>SB</sub></b>	无载条件下估算的转换器效率, 其中不包括启动电阻或偏置损耗。对于一个 5V USB 充电器应用, 60% 到 65% 是一个很好的初步估算值。
<b>η</b>	转换器总体效率。
<b>η<sub>XFMR</sub></b>	变压器一次侧与二次侧之间的功率传输效率。

## 11.2 文档支持

### 11.2.1 相关文档

相关文档如下：

《使用 UCC28700EVM-068, 评估模块》，[SLUU968](#)

## 11.3 商标

All trademarks are the property of their respective owners.

## 11.4 静电放电警告



这些装置包含有限的内置 ESD 保护。存储或装卸时，应将导线一起截短或将装置放置于导电泡棉中，以防止 MOS 门极遭受静电损伤。

## 12 机械封装和可订购信息

以下页中包括机械封装和可订购信息。 这些信息是针对指定器件可提供的最新数据。 这些数据会在无通知且不对本文档进行修订的情况下发生改变。 欲获得该数据表的浏览器版本，请查阅左侧的导航栏。

**PACKAGING INFORMATION**

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
UCC28700QDBVRQ1	ACTIVE	SOT-23	DBV	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	700Q	Samples

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "-" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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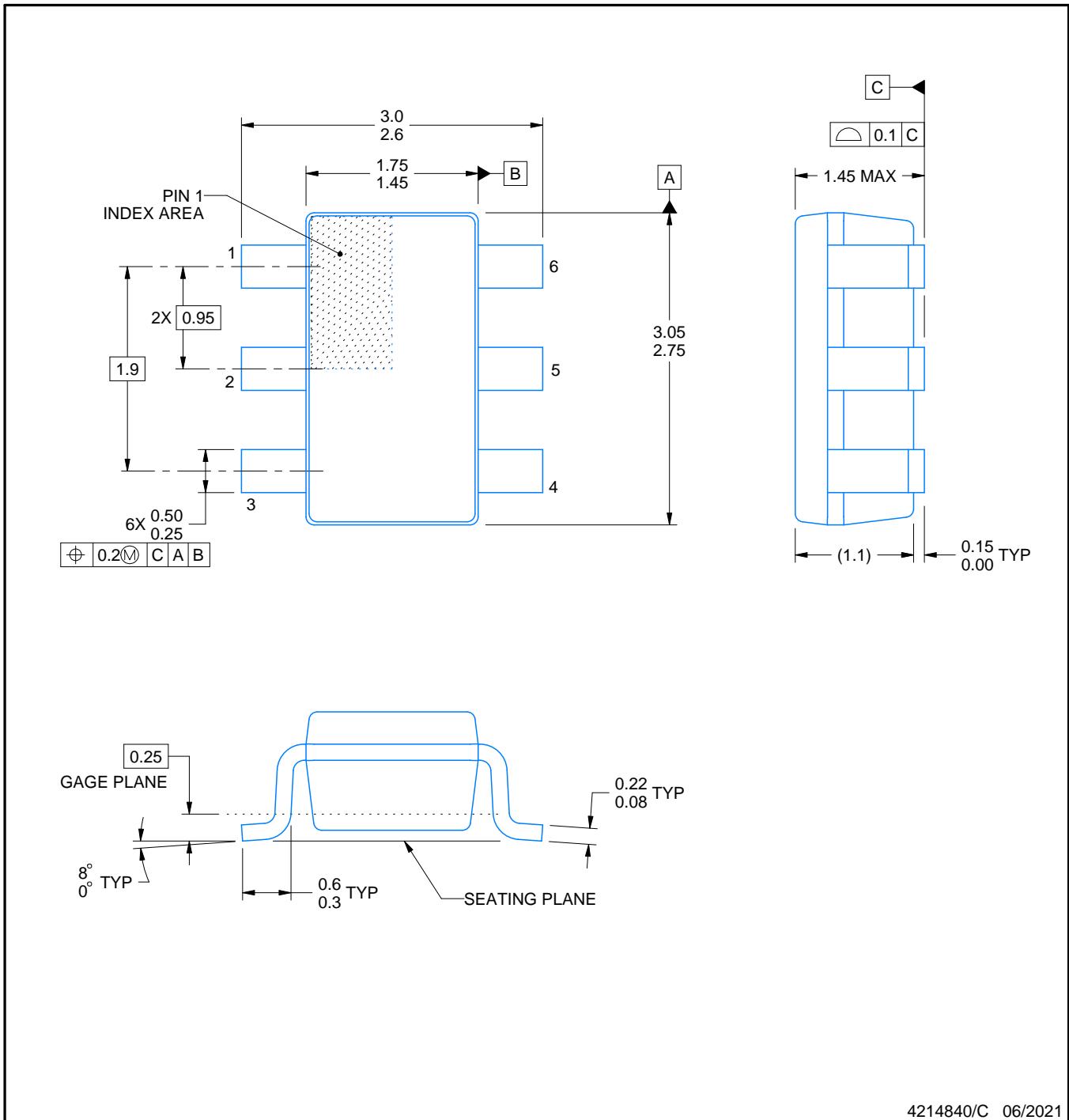
DBV0006A



# PACKAGE OUTLINE

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



4214840/C 06/2021

## NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.25 per side.
4. Leads 1,2,3 may be wider than leads 4,5,6 for package orientation.
5. Reference JEDEC MO-178.

# EXAMPLE BOARD LAYOUT

DBV0006A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



LAND PATTERN EXAMPLE  
EXPOSED METAL SHOWN  
SCALE:15X



SOLDER MASK DETAILS

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NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

# EXAMPLE STENCIL DESIGN

DBV0006A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



SOLDER PASTE EXAMPLE  
BASED ON 0.125 mm THICK STENCIL  
SCALE:15X

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NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

## 重要声明和免责声明

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